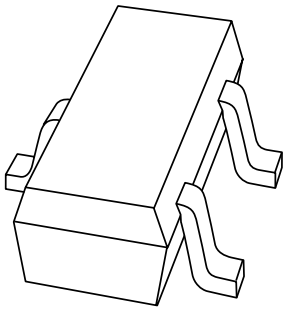
DATA SHEET



PRF949
UHF wideband transistor

Product specification
Supersedes data of 1999 Nov 02

2000 Apr 03

Philips
Semiconductors

PHILIPS

UHF wideband transistor PRF949

FEATURES

- Small size
- Low noise
- Low distortion
- High gain
- Gold metallization ensures excellent reliability.

APPLICATIONS

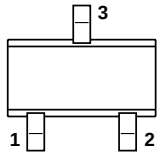
- Communication and instrumentation systems.

DESCRIPTION

Silicon NPN transistor in a surface mount 3-pin SOT416 (SC-75) package. The transistor is primarily intended for wideband applications in the GHz range in the RF front end of analog and digital cellular telephones, cordless phones, radar detectors, pagers and satellite TV-tuners.

PINNING SOT416 (SC-75)

PIN	DESCRIPTION
1	base
2	emitter
3	collector



Top view MBK090

Marking code: V0.

Fig.1 Simplified outline (SOT416).

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
C_{re}	feedback capacitance	I_C = 0; V_{CB} = 6 V; f = 1 MHz	–	0.3	–	pF
f_T	transition frequency	I_C = 15 mA; V_{CE} = 6 V; f_m = 1 GHz	7	9	–	GHz
G_{UM}	maximum unilateral power gain	I_C = 15 mA; V_{CE} = 6 V; T_{amb} = 25 °C; f = 1 GHz	–	16	–	dB
NF	noise figure	$\Gamma_S = \Gamma_{opt}$; I_C = 5 mA; V_{CE} = 6 V; f = 1 GHz	–	1.5	2.5	dB
P_{tot}	total power dissipation	T_s = 75 °C; note 1	–	–	150	mW
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point		–	–	500	K/W

Note

1. T_s is the temperature at the soldering point of the collector pin.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	10	V
V_{EBO}	emitter-base voltage	open collector	–	1.5	V
I_C	collector current (DC)		–	50	mA
$I_{C(AV)}$	average collector current		–	50	mA
P_{tot}	total power dissipation	T_s = 75 °C; note 1	–	150	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. T_s is the temperature at the soldering point of the collector pin.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	500	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
DC characteristics						
$V_{(BR)CBO}$	collector-base breakdown voltage	I_C = 100 μA; I_E = 0	20	–	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	I_C = 100 μA; I_B = 0	10	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	I_E = 10 μA; I_C = 0	1.5	–	–	V
V_{BEF}	forward base-emitter voltage	I_E = 25 mA	–	–	1.05	V
I_{CBO}	collector-base leakage current	V_{CB} = 10 V; I_E = 0	–	–	100	nA
I_{EBO}	emitter-base leakage current	V_{EB} = 1 V; I_C = 0	–	–	100	nA
h_{FE}	DC current gain	I_C = 5 mA; V_{CE} = 6 V	100	150	200	
		I_C = 15 mA; V_{CE} = 6 V	–	150	–	
AC characteristics						
C_{re}	feedback capacitance	I_C = 0; V_{CB} = 6 V; f = 1 MHz	–	0.3	–	pF
f_T	transition frequency	I_C = 15 mA; V_{CE} = 6 V; f_m = 1 GHz	7	9	–	GHz
$\|s_{21}\|^2$	insertion gain	I_C = 15 mA; V_{CE} = 6 V; f = 1 GHz	13	15	–	dB
G_{UM}	maximum unilateral power gain; note 1	I_C = 15 mA; V_{CE} = 6 V; T_{amb} = 25 °C; f = 1 GHz	–	16	–	dB
		I_C = 15 mA; V_{CE} = 6 V; T_{amb} = 25 °C; f = 2 GHz	–	10	–	dB
NF	noise figure	$\Gamma_S = \Gamma_{opt}$; I_C = 5 mA; V_{CE} = 6 V; f = 1 GHz	–	1.5	2.5	dB
		$\Gamma_S = \Gamma_{opt}$; I_C = 5 mA; V_{CE} = 6 V; f = 2 GHz	–	2.1	–	dB

Note

1. G_{UM} is the maximum unilateral power gain, assuming s_{12} is zero. $G_{UM} = 10 \log \frac{|s_{21}|^2}{(1-|s_{11}|^2)(1-|s_{22}|^2)}$ dB

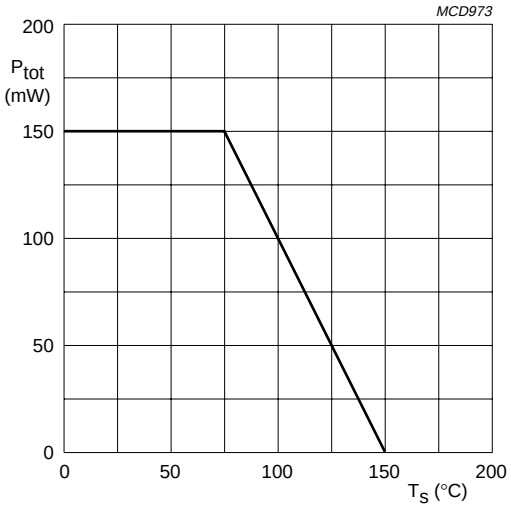
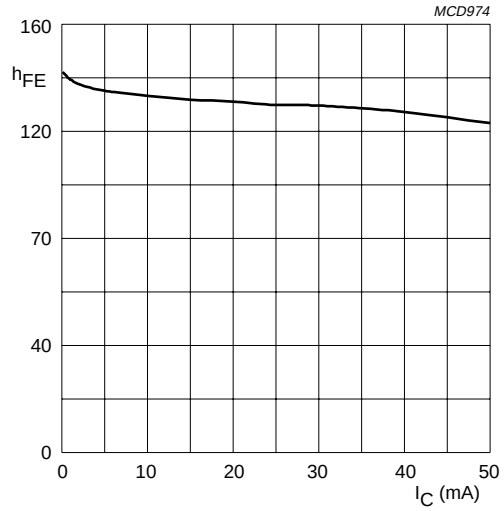
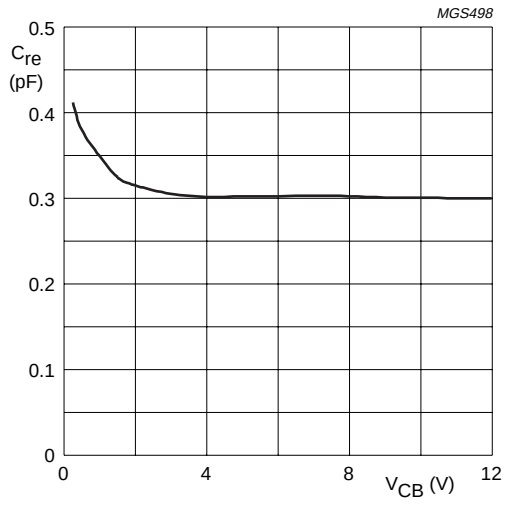


Fig.2 Power derating as a function of soldering point temperature.



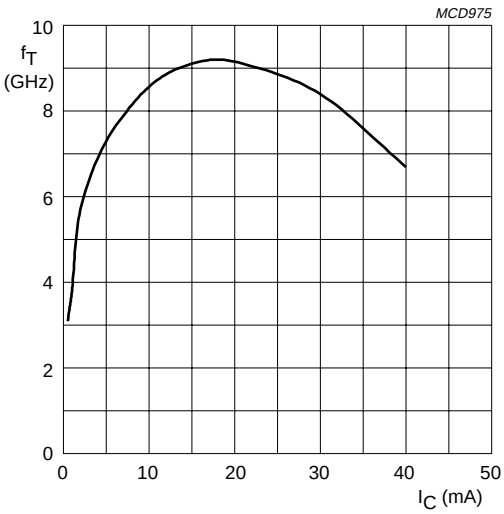
V_{CE} = 6 V.

Fig.3 DC current gain as a function of collector current; typical values.



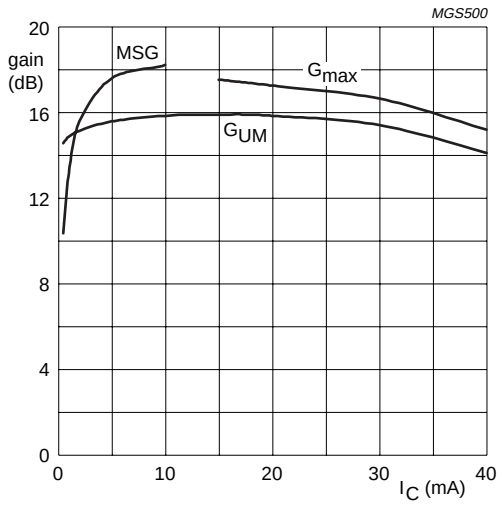
$I_C = I_c = 0$; f = 1 MHz.

Fig.4 Feedback capacitance as a function of collector-base voltage; typical values.



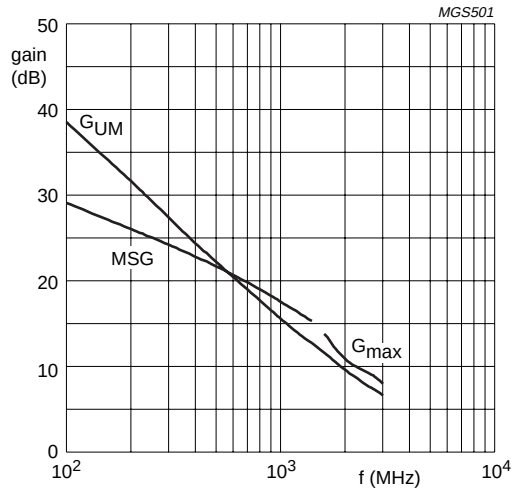
V_{CE} = 6 V; f_m = 1 GHz; T_{amb} = 25 °C.

Fig.5 Transition frequency as a function of collector current; typical values.



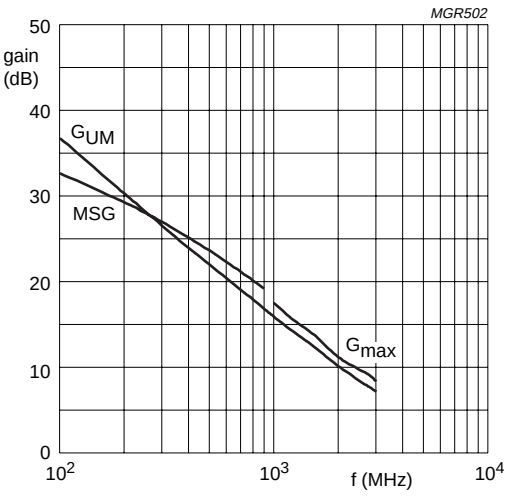
f = 1 GHz; V_{CE} = 6 V.
G_{UM} = maximum unilateral power gain.
MSG = maximum stable gain.
G_{max} = maximum available gain.

Fig.6 Gain as a function of collector current; typical values.



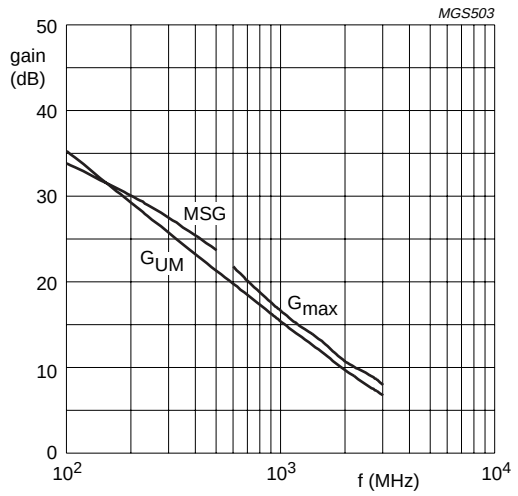
I_C = 5 mA; V_{CE} = 6 V.
G_{UM} = maximum unilateral power gain.
MSG = maximum stable gain.
G_{max} = maximum available gain.

Fig.7 Gain as a function of frequency; typical values.



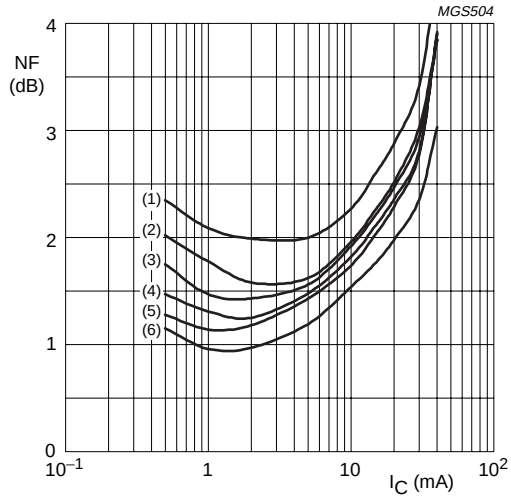
I_C = 15 mA; V_{CE} = 6 V.
G_{UM} = maximum unilateral power gain.
MSG = maximum stable gain.
G_{max} = maximum available gain.

Fig.8 Gain as a function of frequency; typical values.



I_C = 30 mA; V_{CE} = 6 V.
G_{UM} = maximum unilateral power gain.
MSG = maximum stable gain.
G_{max} = maximum available gain.

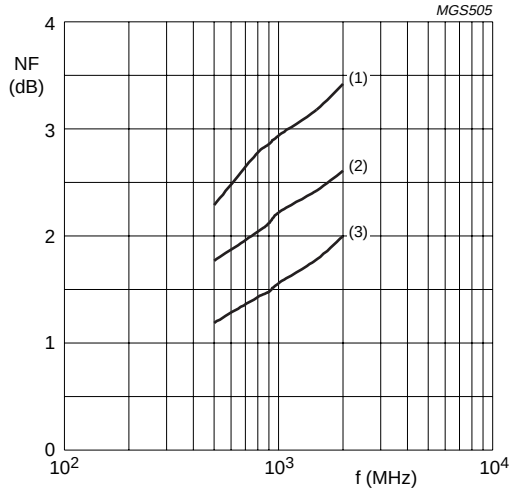
Fig.9 Gain as a function of frequency; typical values.



V_{CE} = 6 V.

(1) f = 2 GHz.
(2) f = 1.5 GHz.
(3) f = 1 GHz.
(4) f = 900 MHz.
(5) f = 800 MHz.
(6) f = 500 MHz.

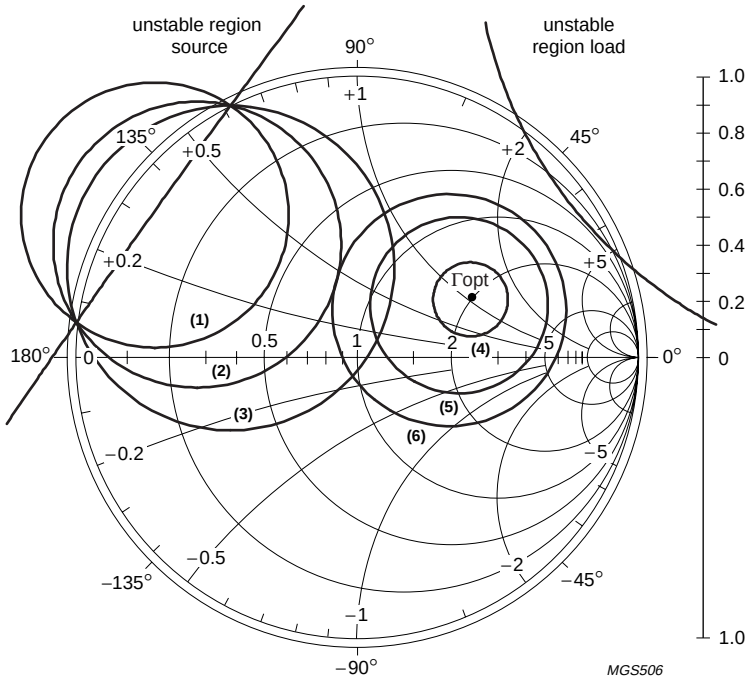
Fig.10 Minimum noise figure as a function of collector current; typical values.



V_{CE} = 6 V.

(1) I_C = 30 mA.
(2) I_C = 15 mA.
(3) I_C = 5 mA.

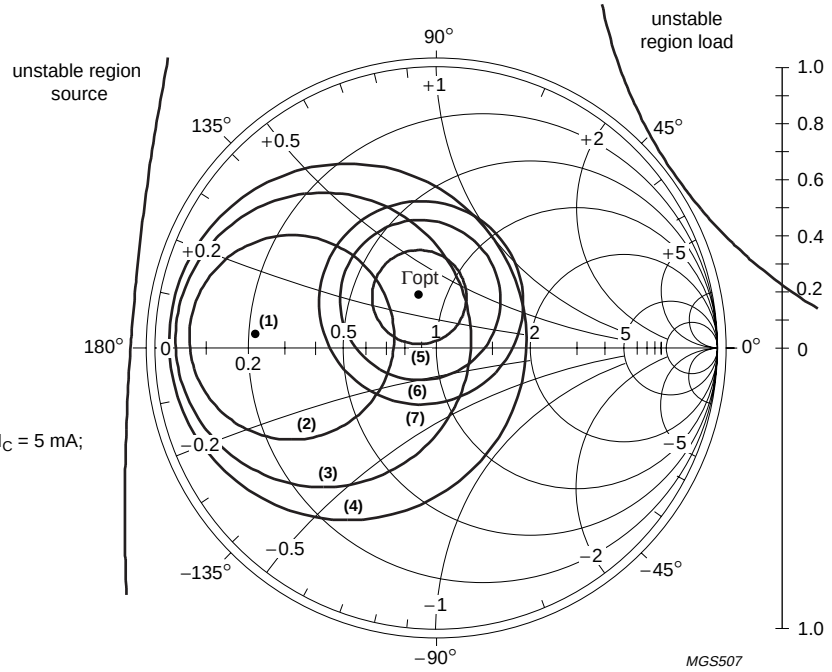
Fig.11 Minimum noise figure as a function of frequency; typical values.



f = 1 GHz; V_{CE} = 6 V; I_C = 5 mA; Z_o = 50 Ω.

(1) G = 17 dB.
(2) G = 16 dB.
(3) G = 15 dB.
(4) NF = 1.6 dB.
(5) NF = 1.8 dB.
(6) NF = 2 dB.

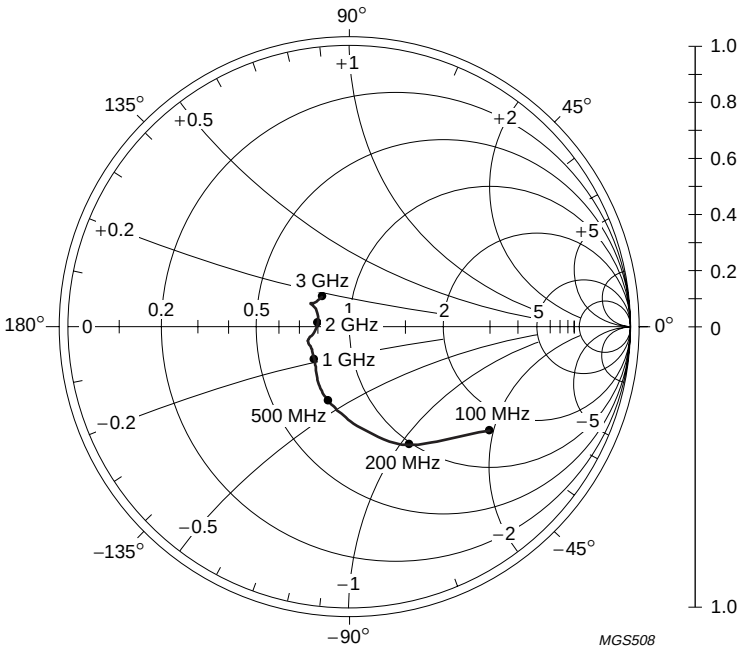
Fig.12 Common emitter available gain, noise and stability circles; typical values.



f = 2 GHz; V_{CE} = 6 V; I_C = 5 mA; Z_o = 50 Ω.

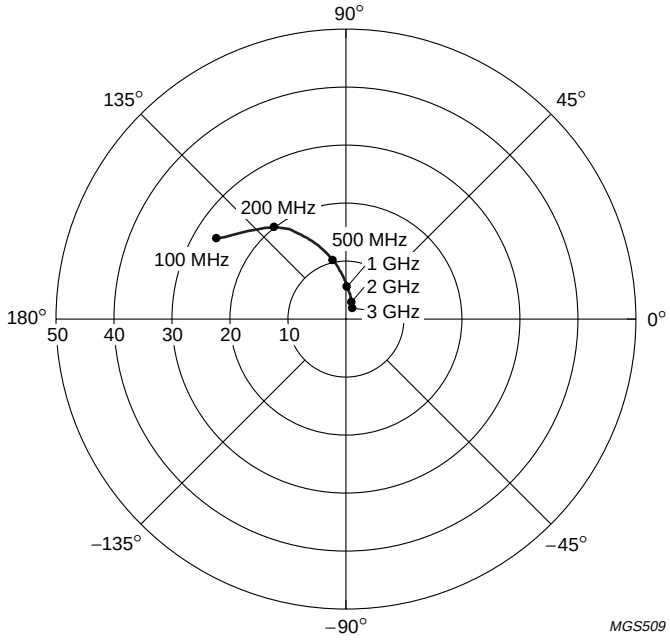
(1) G_{max} = 10.9 dB.
(2) G = 10 dB.
(3) G = 9 dB.
(4) G = 8 dB.
(5) NF = 2.1 dB.
(6) NF = 2.3 dB.
(7) NF = 2.5 dB.

Fig.13 Common emitter available gain, noise and stability circles; typical values.



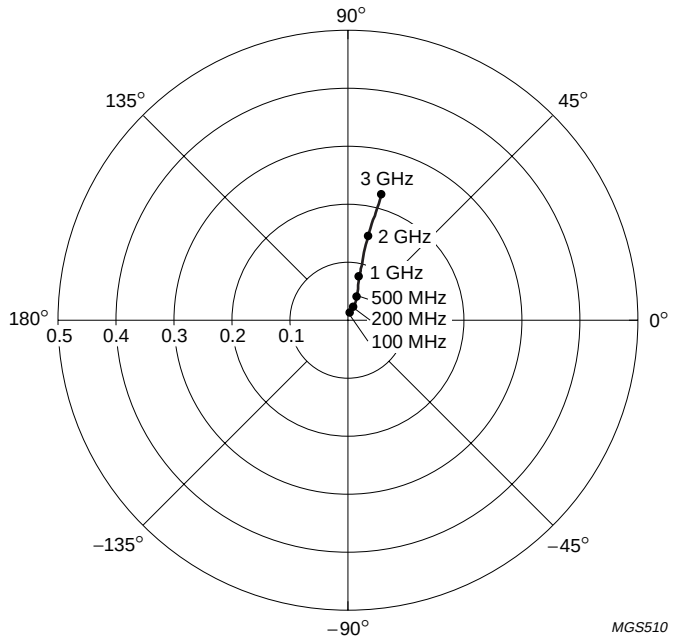
V_{CE} = 6 V; I_C = 15 mA; Z_o = 50 Ω.

Fig.14 Common emitter input reflection coefficient (s_{11}); typical values.



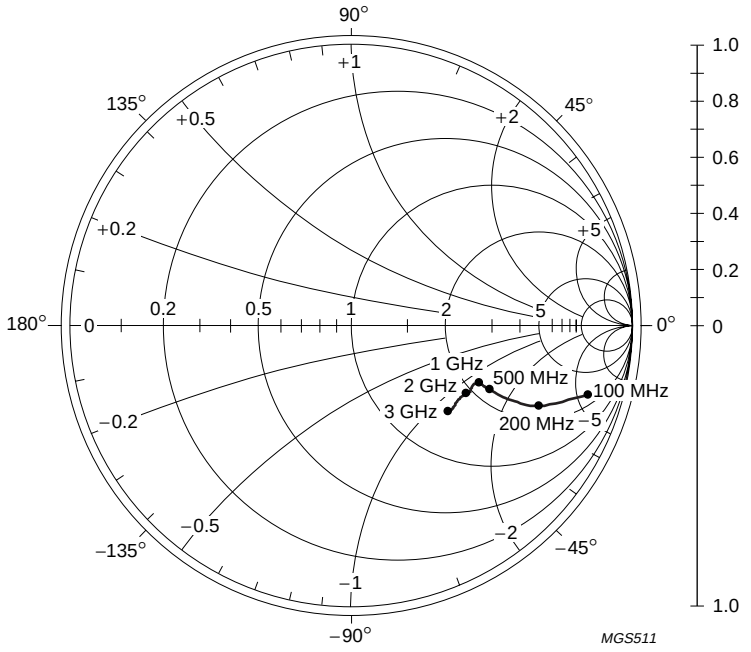
V_{CE} = 6 V; I_C = 15 mA.

Fig.15 Common emitter forward transmission coefficient (s_{21}); typical values.



V_{CE} = 6 V; I_C = 15 mA.

Fig.16 Common emitter reverse transmission coefficient (s_{12}); typical values.

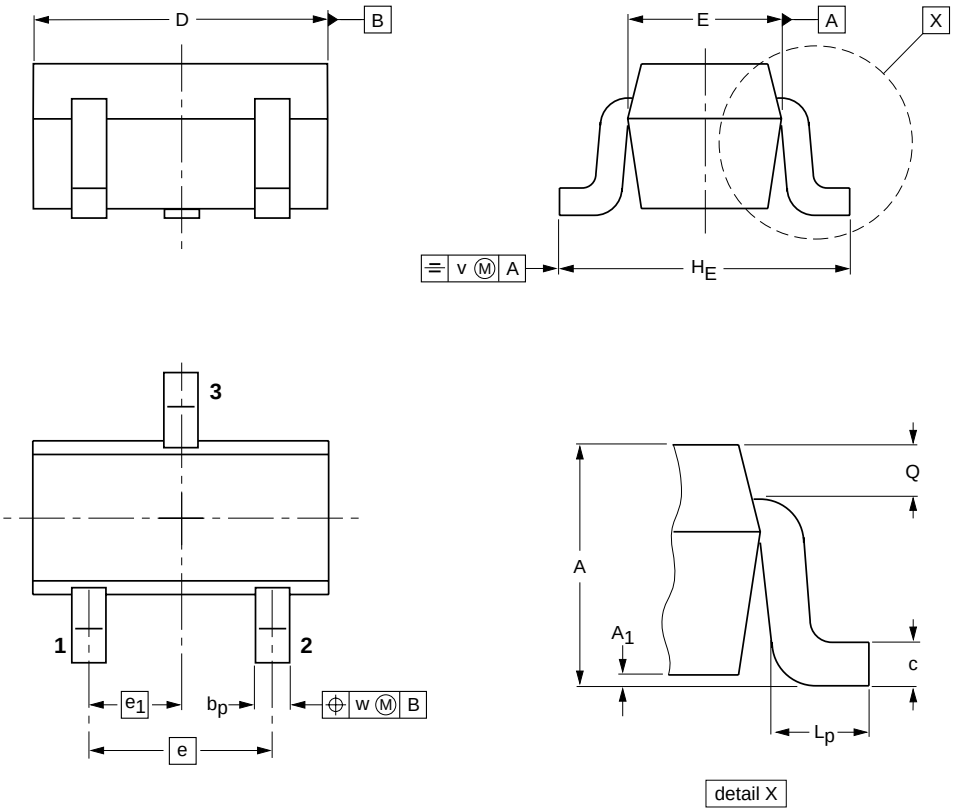


V_{CE} = 6 V; I_C = 15 mA; Z_o = 50 Ω.

Fig.17 Common emitter output reflection coefficient (s_{22}); typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT416**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT416			SC-75			97-02-28

DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS (1)
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

Note

1. Please consult the most recently issued data sheet before initiating or completing a design.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 3 Figtree Drive, HOMEBUSH, NSW 2140,
Tel. +61 2 9704 8141, Fax. +61 2 9704 8139

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,
Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

Belgium: see The Netherlands

Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 68 9211, Fax. +359 2 68 9102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Sydhavnsgade 23, 1780 COPENHAGEN V,
Tel. +45 33 29 3333, Fax. +45 33 29 3905

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. +358 9 615 800, Fax. +358 9 6158 0920

France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex,
Tel. +33 1 4099 6161, Fax. +33 1 4099 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 2353 60, Fax. +49 40 2353 6300

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor,
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,
Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: PT Philips Development Corporation, Semiconductors Division,
Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510,
Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Via Casati, 23 - 20052 MONZA (MI),
Tel. +39 039 203 6838, Fax +39 039 203 6800

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku,
TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5057

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381, Fax +9-5 800 943 0087

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Pakistan: see Singapore

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Al.Jerozolimskie 195 B, 02-222 WARSAW,
Tel. +48 22 5710 000, Fax. +48 22 5710 001

Portugal: see Spain

Romania: see Italy

Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 319762,
Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria

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South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 58088 Newville 2114,
Tel. +27 11 471 5401, Fax. +27 11 471 5398

South America: Al. Vicente Pinzon, 173, 6th floor,
04547-130 SÃO PAULO, SP, Brazil,
Tel. +55 11 821 2333, Fax. +55 11 821 2382

Spain: Balmes 22, 08007 BARCELONA,
Tel. +34 93 301 6312, Fax. +34 93 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,
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Tel. +41 1 488 2741 Fax. +41 1 488 3263

Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,
TAIPEI, Taiwan Tel. +886 2 2134 2886, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,
209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260,
Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Yukari Dudullu, Org. San. Blg., 2.Cad. Nr. 28 81260 Umraniye,
ISTANBUL, Tel. +90 216 522 1500, Fax. +90 216 522 1813

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
MIDDLESEX UB3 5BX, Tel. +44 208 730 5000, Fax. +44 208 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

Uruguay: see South America

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Tel. +381 11 3341 299, Fax.+381 11 3342 553

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International Marketing & Sales Communications, Building BE-p, P.O. Box 218,
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